

## **PN5138**



## **PNP General Purpose Amplifier**

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 68. See PN200 for characteristics.

## **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
$V_{CEO}$	Collector-Emitter Voltage	30	V	
V <sub>CBO</sub>	Collector-Base Voltage	30	V	
V <sub>EBO</sub>	Emitter-Base Voltage		V	
Ic	Collector Current - Continuous		mA	
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C	

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

## **Thermal Characteristics**

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		PN5138	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

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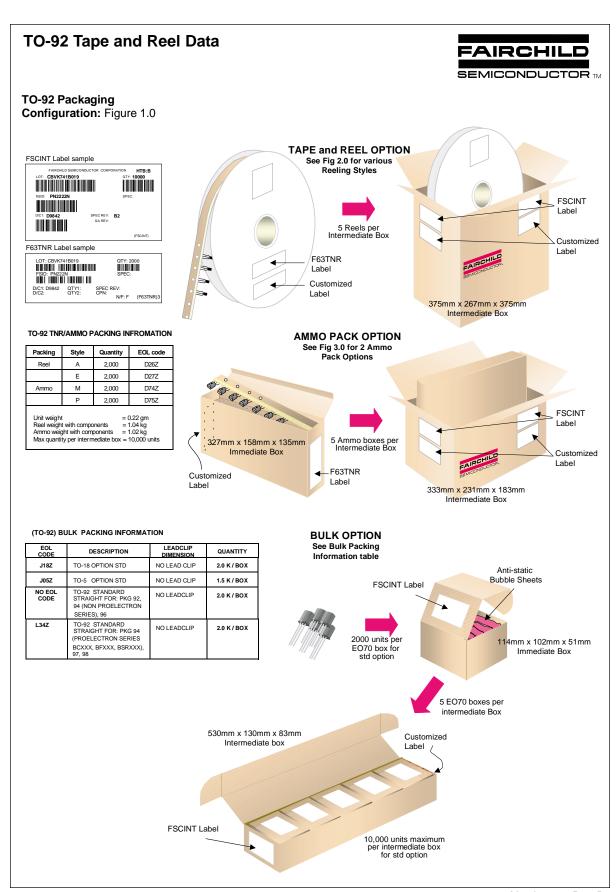
<sup>1)</sup> These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## PNP General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 10 \text{ mA}, I_B = 0$	30		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100 \mu\text{A},  I_E = 0$	30		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 100  \mu A, I_C = 0$	5.0		V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 20 V, I <sub>E</sub> = 0 V <sub>CB</sub> = 20 V, I <sub>E</sub> = 0, T <sub>A</sub> = 65 °C		50 3.0	nA μA
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 10 \text{ V}, I_{C} = 0.1 \mu\text{A}$ $V_{CE} = 10 \text{ V}, I_{C} = 1.0 m\text{A}$ $V_{CE} = 10 \text{ V}, I_{C} = 10 m\text{A}$	50 50 50	800	
		· -			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$		0.3	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$		1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = 10 \text{ V}, I_{C} = 10 \text{ mA}$		1.0	V
SMALL S	IGNAL CHARACTERISTICS				
C <sub>ob</sub>	Output Capacitance	$V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$		7.0	pF
^	Input Capacitance	V <sub>EB</sub> = 0.5 V, f = 1.0 MHz		30	pF
Cib		1 40 1 1/ 40 1/			
C <sub>ib</sub>	Small-Signal Current Gain	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 1.0  kHz $I_C = 0.5 \text{ mA}, V_{CE} = 5.0 \text{ V},$	40	1000	

<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

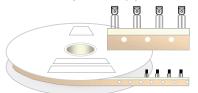


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## TO-92 Tape and Reel Data, continued

## **TO-92 Reeling Style Configuration:** Figure 2.0

## Machine Option "A" (H)

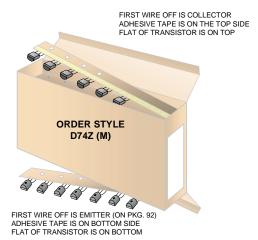


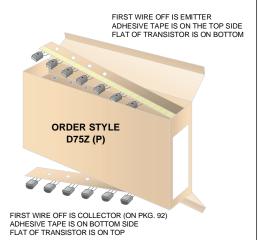
Style "A", D26Z, D70Z (s/h)

# Machine Option "E" (J)

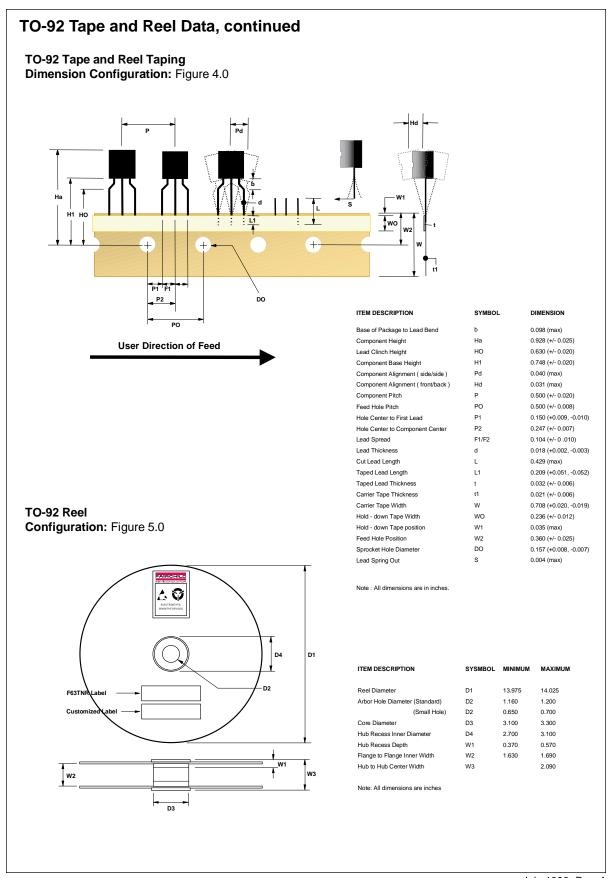
Style "E", D27Z, D71Z (s/h)

## **TO-92 Radial Ammo Packaging Configuration:** Figure 3.0





September 1999, Rev. B



## **TO-92 Package Dimensions** FAIRCHILD SEMICONDUCTOR TM TO-92 (FS PKG Code 92, 94, 96) Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters] Part Weight per unit (gram): 0.1977 0.185 4.70 0.170 4.32 TO-92 (92,94,96) 94 96 B F В В В D D 2 В S С G Ε Ø0.060 [Ø1.52] G В S С G 0.010 [0.254] DEEP 5.0°TYP.

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0.095 0.084 2.13

January 2000, Rev. B

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